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[FDD8N50NZTM](#)

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November 2013



FDD8N50NZ

N-Channel UniFET™ II MOSFET 500 V, 6.5 A, 850 mΩ

Features

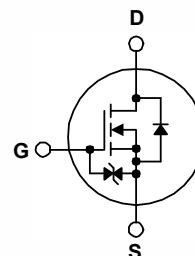
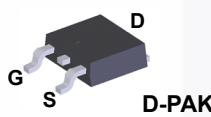
- $R_{DS(on)} = 770 \text{ mΩ}$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 3.25 \text{ A}$
- Low Gate Charge (Typ. 14 nC)
- Low C_{rss} (Typ. 5 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFET™ II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET™ II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDD8N50NZTM	Unit
V_{DSS}	Drain to Source Voltage	500	V
V_{GSS}	Gate to Source Voltage	± 25	V
I_D	Drain Current	6.5	A
	- Continuous ($T_C = 25^\circ\text{C}$)	3.9	
I_{DM}	Drain Current	(Note 1)	A
E_{AS}		26	
E_{AS}		287	mJ
I_{AR}	Avalanche Current	(Note 1)	A
E_{AR}		6.5	
E_{AR}		9	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	V/ns
P_D	Power Dissipation	90	W
	- Derate Above 25°C	0.7	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FDD8N50NZTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.4	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD8N50NZTM	FDD8N50NZ	DPAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}, T_C = 25^\circ\text{C}$	500	-	-	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}, \text{Referenced to } 25^\circ\text{C}$	-	0.5	-	V°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_C = 125^\circ\text{C}$	-	-	10	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	± 10	μA

On Characteristics

$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	3.0	-	5.0	V
$R_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 3.25 \text{ A}$	-	0.77	0.85	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_D = 3.25 \text{ A}$	-	6.3	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	565	735	pF
C_{oss}	Output Capacitance		-	80	105	pF
C_{rss}	Reverse Transfer Capacitance		-	5	8	pF
$Q_{g(\text{tot})}$	Total Gate Charge at 10V	$V_{DS} = 400 \text{ V}, I_D = 6.5 \text{ A}, V_{GS} = 10 \text{ V}$	-	14	18	nC
Q_{gs}	Gate to Source Gate Charge		-	4	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	6	-	nC

Switching Characteristics

$t_{\text{d}(\text{on})}$	Turn-On Delay Time	$V_{DD} = 250 \text{ V}, I_D = 6.5 \text{ A}, R_G = 25 \Omega, V_{GS} = 10 \text{ V}$	-	17	45	ns
t_r	Turn-On Rise Time		-	34	80	ns
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time		-	43	95	ns
t_f	Turn-Off Fall Time		-	27	60	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	30	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 6.5 \text{ A}$	-	-	1.4
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{SD} = 6.5 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$	-	228	-
Q_{rr}	Reverse Recovery Charge	-	1.43	-	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 13.6 \text{ mH}, I_{AS} = 6.5 \text{ A}, V_{DD} = 50 \text{ V}, R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 6.5 \text{ A}, d/dt \leq 200 \text{ A}/\mu\text{s}, V_{DD} \leq \text{BV}_{\text{DSS}}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

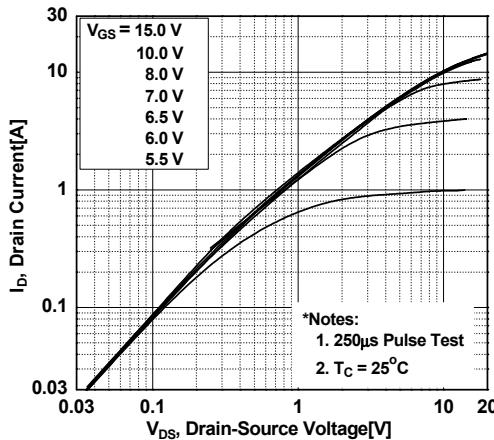


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

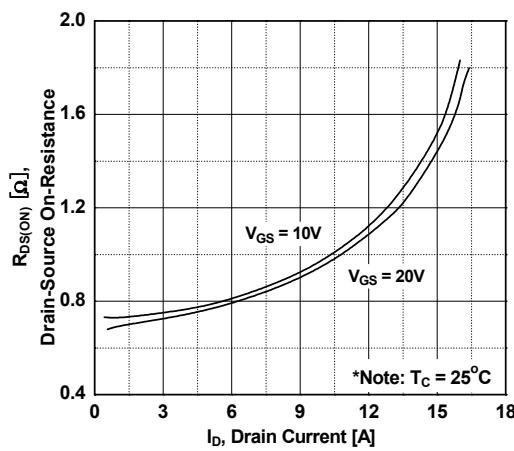


Figure 5. Capacitance Characteristics

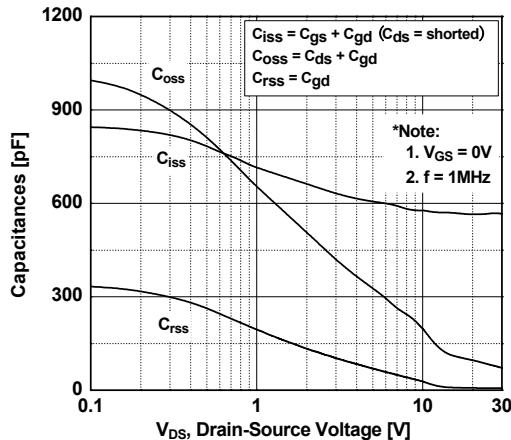


Figure 2. Transfer Characteristics

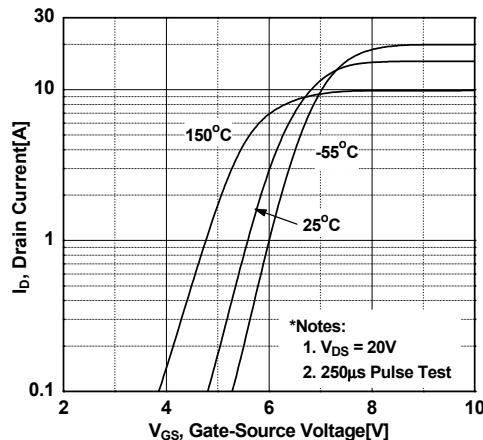


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

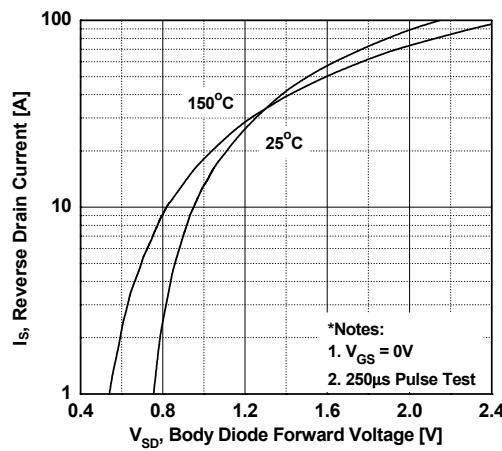
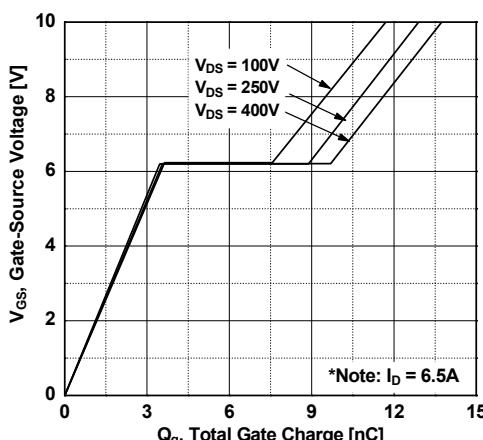


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

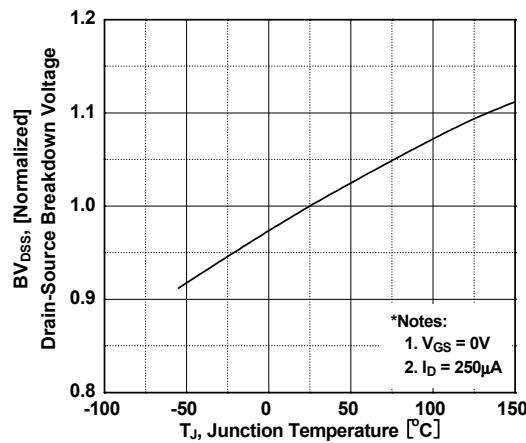


Figure 8. On-Resistance Variation vs. Temperature

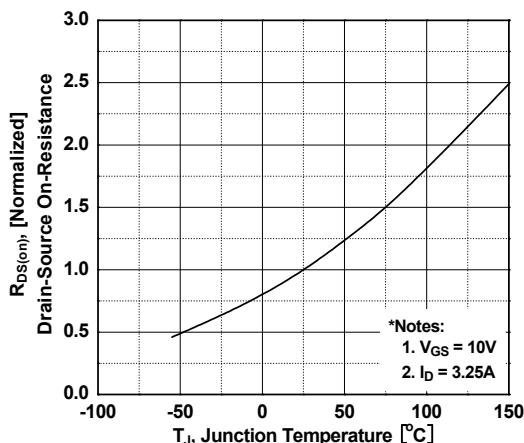


Figure 9. Maximum Safe Operating Area

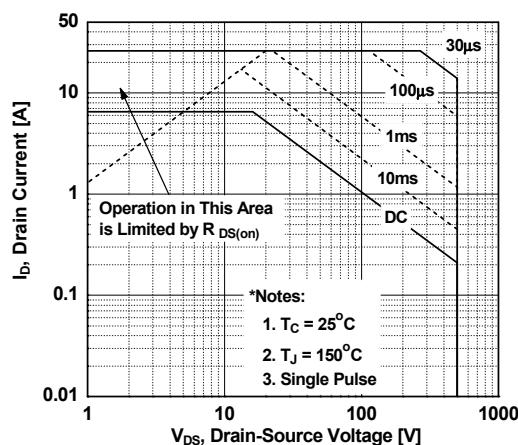


Figure 10. Maximum Drain Current vs. Case Temperature

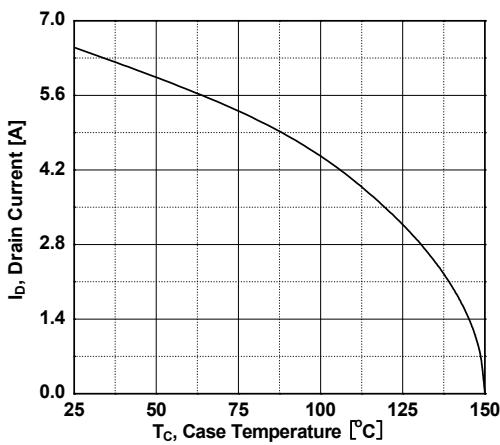
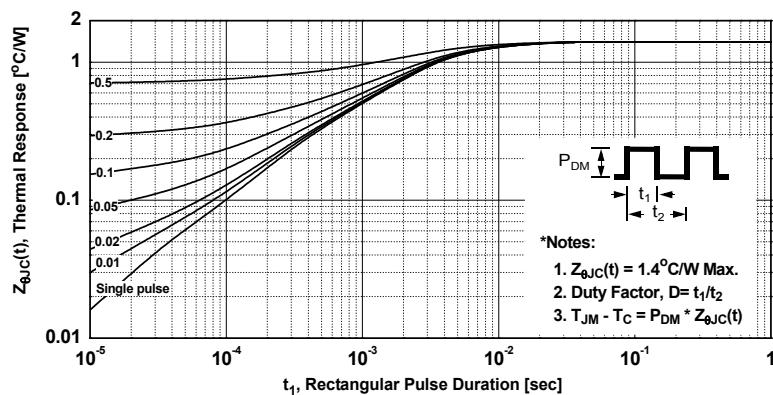


Figure 11. Transient Thermal Response Curve



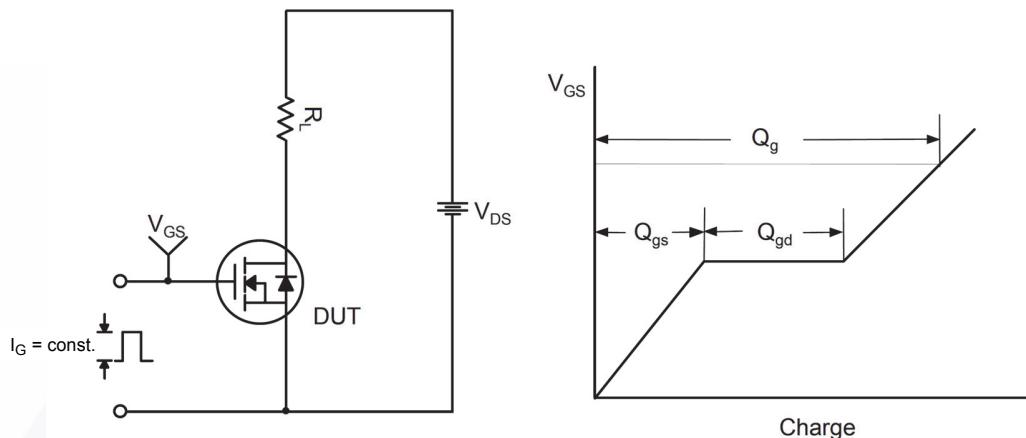


Figure 12. Gate Charge Test Circuit & Waveform

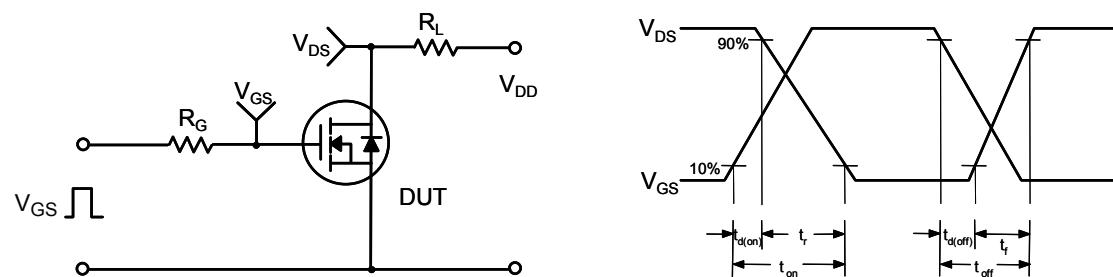


Figure 13. Resistive Switching Test Circuit & Waveforms

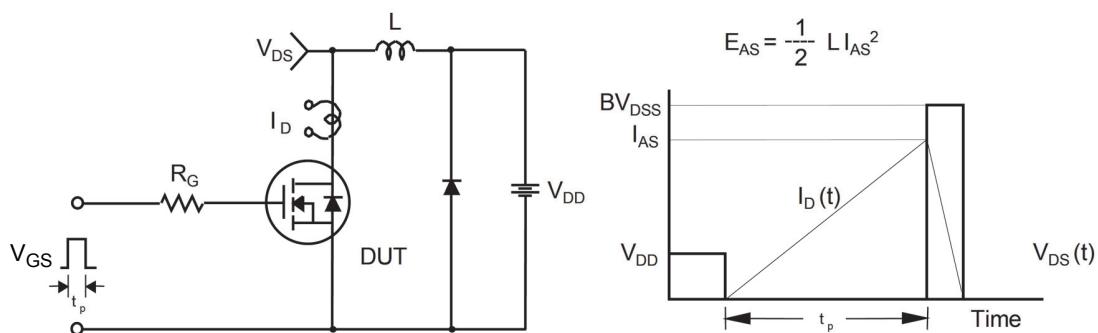


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

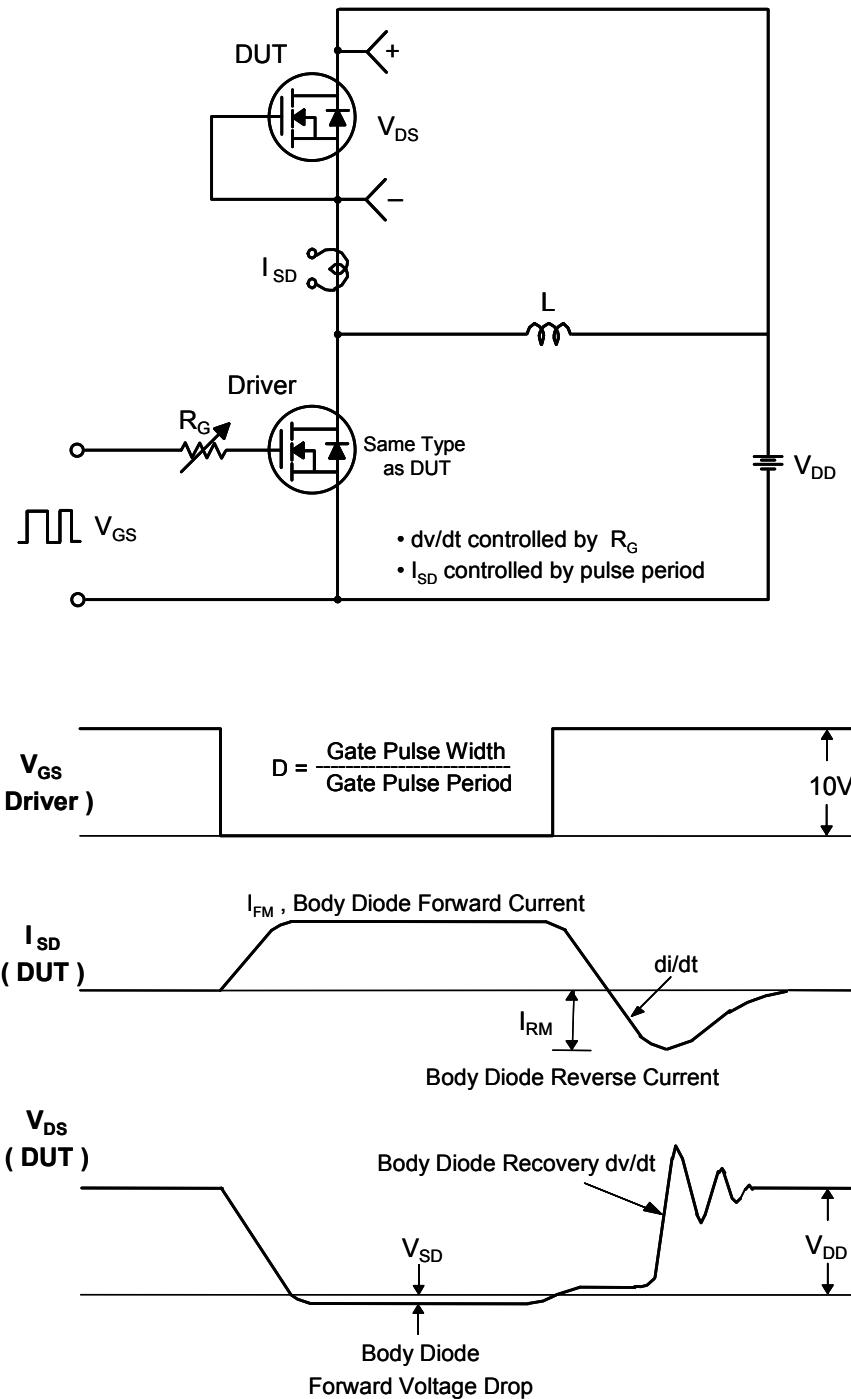


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

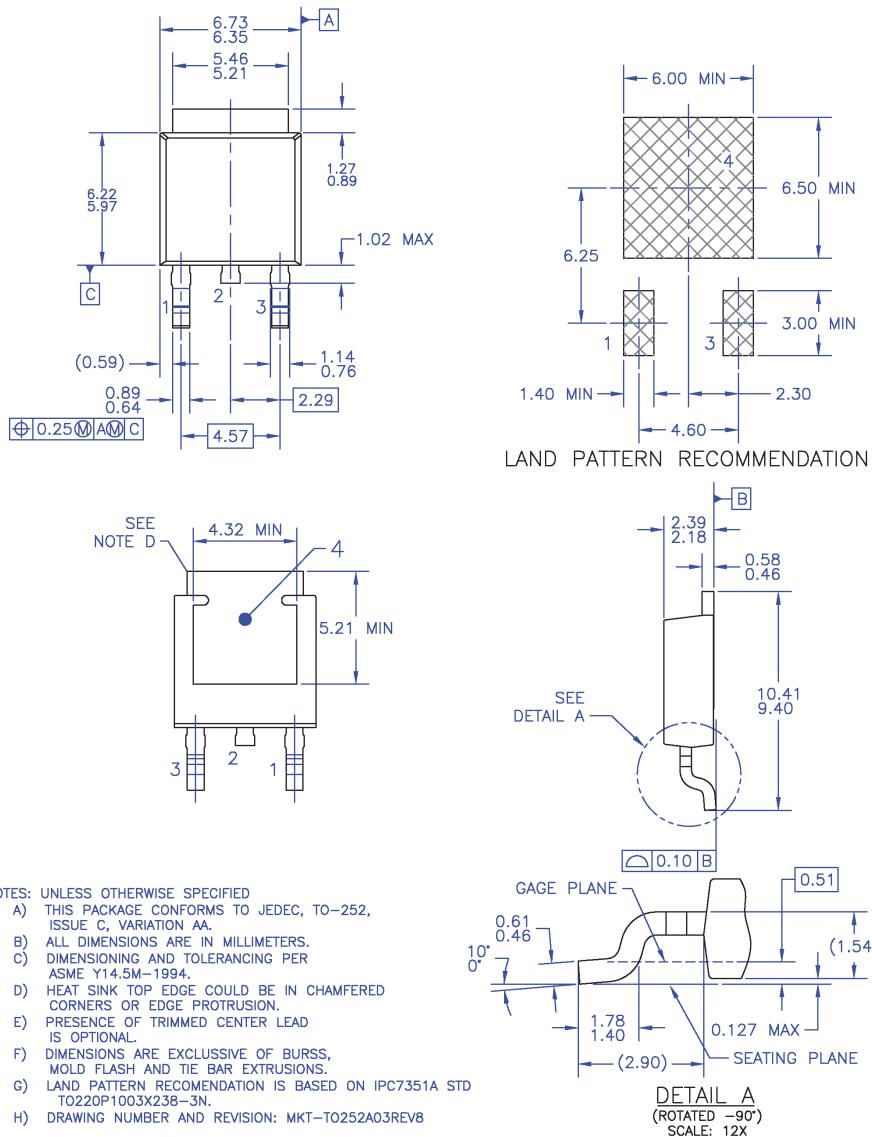


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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